

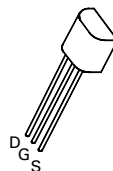
P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVP0540A

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FEATURES

- * 400 Volt V_{DS}
- * $R_{DS(on)}=150\Omega$



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

| PARAMETER | SYMBOL | VALUE | UNIT |
|---|----------------|-------------|-------------|
| Drain-Source Voltage | V_{DS} | -400 | V |
| Continuous Drain Current at $T_{amb}=25^{\circ}C$ | I_D | -45 | mA |
| Pulsed Drain Current | I_{DM} | -400 | mA |
| Gate Source Voltage | V_{GS} | ± 20 | V |
| Power Dissipation at $T_{amb}=25^{\circ}C$ | P_{tot} | 700 | mW |
| Operating and Storage Temperature Range | $T_j; T_{stg}$ | -55 to +150 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

| PARAMETER | SYMBOL | MIN. | MAX. | UNIT | CONDITIONS. |
|---|--------------|------|-----------|---------------|---|
| Drain-Source Breakdown Voltage | BV_{DSS} | -400 | | V | $I_D=-1mA, V_{GS}=0V$ |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | -1.5 | -4.5 | V | $I_D=-1mA, V_{DS}=V_{GS}$ |
| Gate-Body Leakage | I_{GSS} | | 20 | nA | $V_{GS}=\pm 20V, V_{DS}=0V$ |
| Zero Gate Voltage Drain Current | I_{DSS} | | -20 -2 | μA mA | $V_{DS}=-400V, V_{GS}=0$ $V_{DS}=-320V, V_{GS}=0V,$ $T=125^{\circ}C(2)$ |
| On-State Drain Current(1) | $I_{D(on)}$ | -100 | | mA | $V_{DS}=-25V, V_{GS}=-10V$ |
| Static Drain-Source On-State Resistance (1) | $R_{DS(on)}$ | | 150 | Ω | $V_{GS}=-10V, I_D=-50mA$ |
| Forward Transconductance(1)(2) | g_{fs} | 40 | | mS | $V_{DS}=-25V, I_D=-50mA$ |
| Input Capacitance (2) | C_{iss} | | 120 | pF | $V_{DS}=-25V, V_{GS}=0V, f=1MHz$ |
| Common Source Output Capacitance (2) | C_{oss} | | 20 | pF | |
| Reverse Transfer Capacitance (2) | C_{rss} | | 5 | pF | |
| Turn-On Delay Time (2)(3) | $t_{d(on)}$ | | 10 | ns | $V_{DD}=-25V, I_D=-50mA$ |
| Rise Time (2)(3) | t_r | | 15 | ns | |
| Turn-Off Delay Time (2)(3) | $t_{d(off)}$ | | 15 | ns | |
| Fall Time (2)(3) | t_f | | 20 | ns | |

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$